

## FFSH4065A

# Silicon Carbide (SiC) Schottky Diode, 650 V, 40 A, TO-247-2L

## Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

### Features

- Max Junction Temperature 175 °C
- High Surge Current Capacity
- Positive Temperature Coefficient
- No Reverse Recovery / No Forward Recovery
- Pb-Free, Halogen Free/BFR Free and RoHS Compliant

### Applications


- Telecommunication
- Cloud system
- Industrial

### Benefits

- High system reliability in high ambient temperature
- High system reliability
- Ease of Paralleling
- Low switching loss

### End Products

- Telecom power
- Server power
- UPS / ESS
- Solar inverter
- EV Charger

Part Electrical Specifications											
Product	Pricing (\$/Unit)	Compliance	Status	Family	Configuration	V <sub>RRM</sub> (V)	I <sub>F(ave)</sub> (A)	V <sub>F</sub> (Max)	I <sub>FSM</sub> (A)	I <sub>R</sub> (Max) (µA)	Package Type
FFSH4065A	7.6974	 	Active	D1	Single	650	40	1.75	180	200	TO-247-2